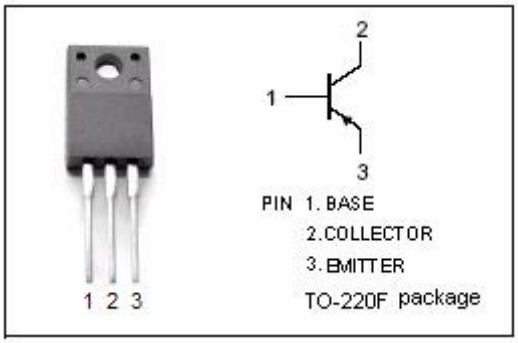
# isc Silicon PNP Power Transistor KTB1369

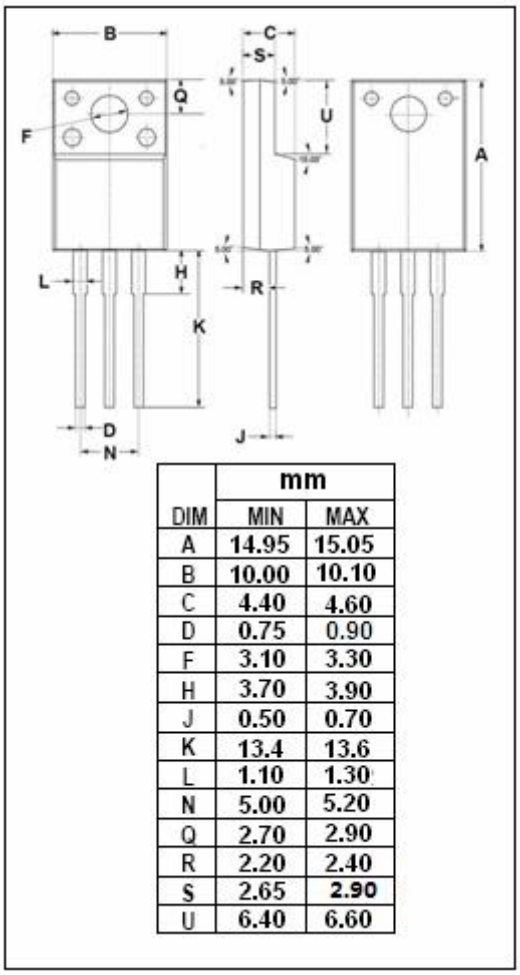
## DESCRIPTION

- High Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= -180V(Min)
- Low Collector Saturation Voltage-
  : $V_{CE(sat)}$= −1.0V(Max)@ ($I_C$= -0.5A, $I_B$= -50mA)
- Complement to Type KTD2061




## APPLICATIONS

- High Voltage application
- TV, monitor vertical output application
- Driver stage application
- Color TV class B sound output application




| DIM | mm MIN | MAX |
|---|---|---|
| A | 14.95 | 15.05 |
| B | 10.00 | 10.10 |
| C | 4.40 | 4.60 |
| D | 0.75 | 0.90 |
| F | 3.10 | 3.30 |
| H | 3.70 | 3.90 |
| J | 0.50 | 0.70 |
| K | 13.4 | 13.6 |
| L | 1.10 | 1.30 |
| N | 5.00 | 5.20 |
| Q | 2.70 | 2.90 |
| R | 2.20 | 2.40 |
| S | 2.65 | 2.90 |
| U | 6.40 | 6.60 |

## ABSOLUTE MAXIMUM RATINGS($T_a$=25℃)

| SYMBOL | PARAMETER | VALUE | UNIT |
|---|---|---|---|
| $V_{CBO}$ | Collector-Base Voltage | -200 | V |
| $V_{CEO}$ | Collector-Emitter Voltage | -180 | V |
| $V_{EBO}$ | Emitter-Base Voltage | -5 | V |
| $I_C$ | Collector Current-Continuous | -2 | A |
| $I_B$ | Base Current-Continuous | -0.2 | A |
| $P_C$ | Collector Power Dissipation @$T_C$=25℃ | 20 | W |
| $T_J$ | Junction Temperature | 150 | ℃ |
| $T_{stg}$ | Storage Temperature | -55~150 | ℃ |

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## ELECTRICAL CHARACTERISTICS

**Tj=25℃ unless otherwise specified**

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|---|---|---|---|---|---|---|
| $V_{(BR)CEO}$ | Collector-Emitter Breakdown Voltage | $I_C$= -10mA; $I_B$= 0 | -180 | | | V |
| $V_{CE(sat)}$ | Collector-Emitter Saturation Voltage | $I_C$= -0.5A; $I_B$= -50mA | | | -1.0 | V |
| $V_{BE(on)}$ | Base-Emitter On Voltage | $I_C$= -0.5A; $V_{CE}$= -5V | | | -1.0 | V |
| $I_{CBO}$ | Collector Cutoff Current | $V_{CB}$= -200V; $I_E$= 0 | | | -1.0 | μA |
| $I_{EBO}$ | Emitter Cutoff Current | $V_{EB}$= -5V; $I_C$= 0 | | | -1.0 | μA |
| $h_{FE}$ | DC Current Gain | $I_C$= -0.4A; $V_{CE}$= -10V | 70 | | 240 | |
| $f_T$ | Current-Gain—Bandwidth Product | $I_C$= -0.4A; $V_{CE}$= -10V | | 100 | | MHz |

◆ **$h_{FE}$ Classification**

| O | Y |
|---|---|
| 70-140 | 120-240 |